Structural Transition of Alkylthiol/Au(111) Interface During Self-assembly Process Kohei Uosaki,^{1,2,3} and Toshihiro Kondo⁴ ¹International Center for Materials Nanoarchitectonics (WPI-MANA), National Institute for Materials Science (NIMS), Tsukuba 305-0044, Japan.

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Construction of well-ordered organic molecular layers on solid surfaces has been the subject of numerous studies because of their importance both in fundamental science and for a wide range of applications such as molecular and bio-electronic devices. Self-assembly (SA) technique is proved to be one of the best methods to construct ordered molecular layer on solid surfaces to provide functional surface. Self-assembled monolayers (SAMs) of alkylthiols on gold have been extensively studied because stable monolayers with high packing density, stability, and orientational order can be very easily formed by soaking a substrate in solution containing alkylthiol molecules. Surface properties can be controlled by forming SAMs of alkylthiols with terminal functional groups.¹⁻³

In order to construct the highly efficient molecular devices using SAMs, we have to construct the wellordered SAMs on Au(111) and it is essential to understand and to control the SA process of the alkylthiol on a Au(111) surface.¹⁻⁷ Not only the structure of the SAM of full coverage but also formation processes of the alkylthiol SAMs on Au(111), which are grown both from solution or from the gas-phase, have been extensively studied experimentally and theoretically but there are many discrepancies between experimental results and theoretical models. Furthermore, alkylthiol SAMs on Au(111) have some defects such as a missing row (boundary defect) and vacancy island (etch pit) and their formation mechanisms have not been made clear completely yet.

Surface X-ray scattering (SXS) technique is one of the best methods to precisely determine the interfacial atomic arrangements with a high spatial resolution and has been employed to monitor the change of the surface atomic arrangements of the Au(111) surface from the $(23 \times \sqrt{3})$ reconstructed structure to the (1×1) structure under electrochemical condition *in situ.*^{8,9}

Here, the transition of the atomic arrangement of Au(111) surface from the reconstructed ($\sqrt{3}\times23$) to the (1×1) structure during the hexylthiol (C₆SH) SAM formation was investigated by monitoring in-plane SXS, i.e., surface X-ray diffraction (SXRD), profiles of the C₆SH SAM modified Au(111) with various surface densities of the SAM, Γ , which were determined by the electrochemical reductive desorption of the SAM.¹⁰

Detailed electrochemical and surface X-ray diffraction measurements shows that the Au(111)-($23\times\sqrt{3}$) reconstructed structure is converted to the Au(111)-(1×1) structure upon the formation of a hexylthiol SAM but the degree of the lifting of the Au(111) reconstructed structure non-linearly depends on the surface concentration of the thiol SAM, Γ . The reconstruction lifting seems to be induced by the formation of the

condensed phase of the SAM on the Au(111) surface with $(\sqrt{3}x\sqrt{3})R30^\circ$ structure, which takes place when the surface concentration of the adsorbed thiol on the Au(111)-(23× $\sqrt{3}$) reconstructed structure reached the full coverage in the lying-down phase.¹¹

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